

ABSTRACT

[Solution of the Problem According to the Invention]
The reduction of the junction electric field intensity
in the semiconductor regions for the sources and
5 drains of the field effects transistors.

[Method for Solving the Problem] A structure is
provided where the gate electrodes 9 of the MIS•FETQs
for memory cell selection of a DRAM are buried within
the trenches 7a and 7b created in the semiconductor
10 substrate 1. The bottom corners within the trench 7b
are rounded so as to have a radius of curvature in
accordance with the sub-threshold coefficient of the
MIS•FETQs for memory cell selection. In addition, the
gate insulating film 8 within the trench 7b is made to
15 have a laminated structure of a thermal oxide film and
a CVD film.

[Selected Drawing] Fig. 28